



Bipolar NPN Bare Die – BTN049X

Part Description

The BTN049X is a silicon BJT transistor available in bare die form and well suited for use in High Voltage Driver applications.

Key Parameters:

- VCBO = 600V
- VCEO = 400V
- VEBO = 9V
- hFE = 80- @ VCE = 10V, IC = 0.25A
- VCE(Sat) = 1V @ IC = 1A, IB = 250mA
- fT = - MHz @ VCE = - V, IE = - A
- COBO = - pF @ VCB = - V

Features

Die Size (Unsaun)

1500 μ m X 1500 μ m, 59 Mils X 59 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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